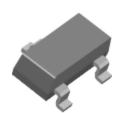
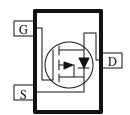
## P - Channel 40V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY				
$V_{DS}(V)$	$\mathbf{r}_{\mathbf{DS}(\mathbf{on})}(\mathbf{O})$ $\mathbf{I}_{\mathbf{D}}(\mathbf{A})$			
-40	$0.164 @ V_{SS} = -10 V$	-3.2		
-40	0.260 @ V <sub>3S</sub> =-4.5V	-2.6		

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Ratings	Units	
Drain-Source Voltage		$V_{DS}$	-40	V	
Gate-Source Voltage			±20	v	
		т	± 3.2		
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ID	± 2.7	A	
Pulsed Drain Current b			±10		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	0.4	A	
$T_{A}=2$		$\mathbb{C}_{\mathbb{D}}$	1.25		
Power Dissipation <sup>a</sup>	$T_A=70^{\circ}C$	$\begin{array}{c c} T_A=25^{\circ}C \\ \hline T_A=70^{\circ}C \end{array} P_D$		W	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
N	t <= 5 sec	D	100	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	$R_{THJA}$	150	

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

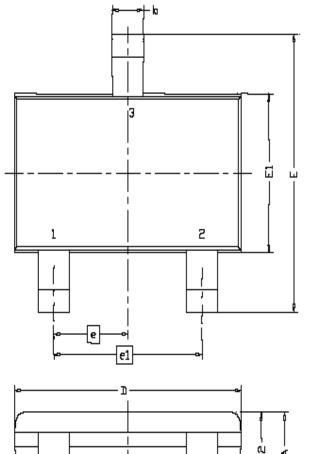
SPECIFICATIONS (T <sub>k</sub> = 25°C UNLESS OTHERWISE NOTED)							
D 4		T C . 144	Limits			<b>T.</b> •	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Switch Off Characteristics					•	•	
Zono Coto Woltogo Dunin Commont	I <sub>DSS</sub>	$V_{DS} = -32 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current		$V_{DS} = -32 \text{ V}, V_{CS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	μA	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 V, V_{CS} = \pm 20 V$			±100	nA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mathrm{uA}$	-1.0			V	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-2			A	
A	r <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, I_D = -3.2 \text{ A}$			164	m?	
Drain-Source On-Resistance		$V_{GS} = -4.5 \text{ V}, I_D = -2.6 \text{ A}$			260		
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	$V_{DS} = -5 \text{ V}, I_{D} = -3.6 \text{ A}$		2		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = -0.4 A, V_{GS} = 0 V$		-0.70		V	
Dynamic <sup>b</sup>					•	•	
Total Gate Charge	$Q_{\!\scriptscriptstyle g}$	$V_{DS} = -10 \text{ V}, V_{GS} = -5 \text{ V},$		15			
Gate-Source Charge	$Q_{gs}$	$I_{D} = -3.6 \text{A}$		2.0		пC	
Gate-Drain Charge	$Q_{gd}$	iрэ.од		2.0			
Turn-On Delay Time	t <sub>d(on)</sub>			10			
RiseTime	t <sub>r</sub>	$V_{DS} = -15 \text{ V}, I_D = -1 \text{ A},$		2.8		ns	
Turn-Off Delay Time	$t_{ m d(off)}$	$R_G = 50 O$ , $V_{GEN} = -10 V$		53.6		1115	
Fall-Time	$t_{\mathrm{f}}$			46			

## Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Package Information



пти	MILLIMETERS			
DIM,	MIN	NDM	MAX	
Α	0.935	0.95	1.10	
A1	0.01	-	0.10	
A2	0.85	0.90	0.925	
Ь	0.30	0.40	0.50	
С	0.10	0.15	0.25	
D	2.70	2.90	3.10	
Ε	2.60	2.80	3.00	
E1	1.40	1.60	1.80	
6	0.95 BSC			
el	1.90 BSC			
L	0.30	0.40	0.60	
L1	0.60REF			
L2	0.25BSC			
R	0.10			
θ	÷	4*	8*	
81	7*N□M			

